

PSMN1R5-40PS

N-channel 40 V 1.6 mΩ standard level MOSFET in TO220
15 July 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in SOT78 (TO220) using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Robust construction for demanding applications
- Standard level gate

3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | | |
|---------------------|----------------------------------|--|-----|-----|-----|-----|------|--|--|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 40 | V | | |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | [1] | - | - | 150 | Α | | |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 338 | W | | |
| Static characte | Static characteristics | | | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 °C;$ Fig. 13 | | - | 1.9 | 2.3 | mΩ | | |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 14 | [2] | - | 1.3 | 1.6 | mΩ | | |
| Dynamic chara | Dynamic characteristics | | | | | | | | |
| Q_{GD} | gate-drain charge | V_{GS} = 10 V; I_D = 75 A; V_{DS} = 20 V; | | - | 32 | - | nC | | |
| Q _{G(tot)} | total gate charge | T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u> | | - | 136 | - | nC | | |



| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|---|--|--|-----|-----|-----|------|
| Avalanche ruggedness | | | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 150 A; $V_{sup} \le$ 40 V; unclamped; R_{GS} = 50 Ω; t_p = 0.1 ms; <u>Fig. 3</u> | | - | - | 1.1 | J |

- [1] Continuous current is limited by package
- [2] Measured 3 mm from package.

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1 | G | gate | mb | D I |
| 2 | D | drain | | |
| 3 | S | source | | G—U: 4 |
| mb | D | drain | | mbb076 S |
| | | | TO-220AB (SOT78) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|--------------|----------|--|---------|--|--|
| | Name | Description | Version | | |
| PSMN1R5-40PS | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| PSMN1R5-40PS | PSMN1R5-40PS |

8. Limiting values

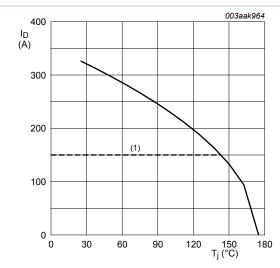
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 40 | V |
| V_{DGR} | drain-gate voltage | $T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ | | - | 40 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u> | [1] | - | 150 | Α |
| | | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | [1] | - | 150 | Α |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 4 | | - | 1301 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 338 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | | - | 260 | °C |
| Source-dra | in diode | | 1 | | | |
| Is | source current | T _{mb} = 25 °C | [1] | - | 150 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 1301 | Α |
| Avalanche | ruggedness | | 1 | 1 | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 150 A; V_{sup} ≤ 40 V; unclamped; R_{GS} = 50 Ω; t_p = 0.1 ms; Fig. 3 | | - | 1.1 | J |

^[1] Continuous current is limited by package

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(1) Capped at 150A due to package

Fig. 1. Normalized continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

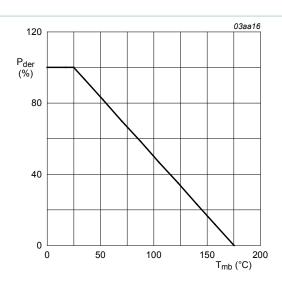


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$

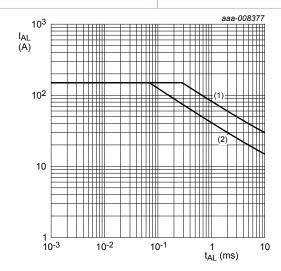


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j\ (init)} = 25^{\circ}C;$$
 (2) $T_{j\ (init)} = 100^{\circ}C$

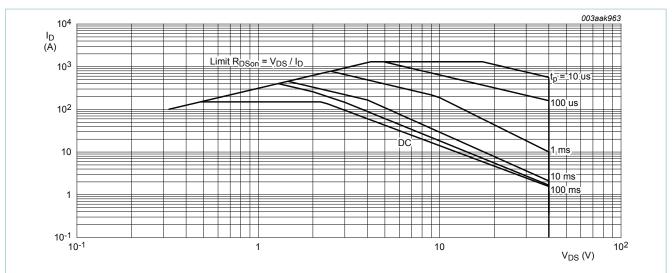


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 T_{mb} = 25 °C; I_{DM} is a single pulse; Capped at 150 A due to package

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|----------------------|-----|------|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | - | 0.22 | 0.44 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | Vertical in free air | - | 60 | - | K/W |

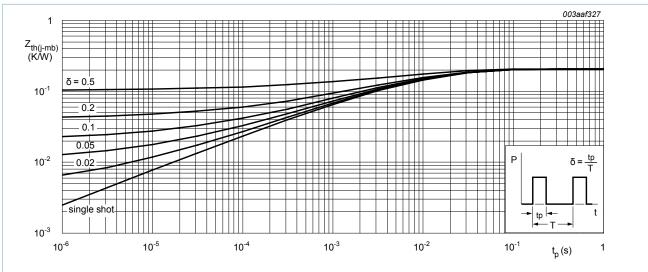


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7 Characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|--|-----|-----|------|-----|------|
| Static chara | acteristics | | | | | | |
| V _{(BR)DSS} | drain-source | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | | 36 | - | - | V |
| | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | | 40 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 11 | | - | - | 4.6 | V |
| | | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 11 | | 1 | - | - | V |
| | | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 12; Fig. 11 | | 2 | 3 | 4 | V |
| I _{DSS} | drain leakage current | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C | | - | 0.02 | 10 | μA |
| | | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C | | - | 250 | 500 | μA |
| I _{GSS} gate leakage current | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | | - | 2 | 100 | nA |
| | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | | - | 2 | 100 | nA | |
| R _{DSon} drain-source on-state resistance | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 °C;$ Fig. 13 | | - | 1.9 | 2.3 | mΩ |
| | | V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 13 | | - | 2.6 | 3.2 | mΩ |
| | | V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 14 | [1] | - | 1.3 | 1.6 | mΩ |
| R_G | internal gate resistance (AC) | f = 1 MHz | | - | 1.1 | - | Ω |
| Dynamic ch | naracteristics | | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V | | - | 133 | - | nC |
| | | I _D = 75 A; V _{DS} = 20 V; V _{GS} = 10 V; | | - | 136 | - | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u> | | - | 52 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | | | - | 30 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate- source charge | | | - | 22.5 | - | nC |
| Q_{GD} | gate-drain charge | | | - | 32 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | I _D = 75 A; V _{DS} = 20 V; T _j = 25 °C; Fig. 15; Fig. 16 | | - | 6.1 | - | V |
| C _{iss} | input capacitance | V _{DS} = 20 V; V _{GS} = 0 V; f = 1 MHz; | | - | 9710 | - | pF |
| C _{oss} | output capacitance | T = 25 °C: Eig. 17 | | - | 2042 | - | pF |

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|------------------------------|---|--|-----|-----|-----|------|
| C _{rss} | reverse transfer capacitance | | | - | 994 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 10 \text{ V};$ | | - | 45 | - | ns |
| t _r | rise time | $R_{G(ext)} = 4.7 \Omega; T_j = 25 ^{\circ}C$ | | - | 66 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | | - | 111 | - | ns |
| t _f | fall time | | | - | 53 | - | ns |
| Source-drain | diode | | | 1 | ' | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 18$ | | - | 8.0 | 1.2 | V |
| t _{rr} | reverse recovery time | I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C | | - | 64 | - | ns |
| Q _r | recovered charge | I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C | | - | 117 | - | nC |

[1] Measured 3 mm from package.

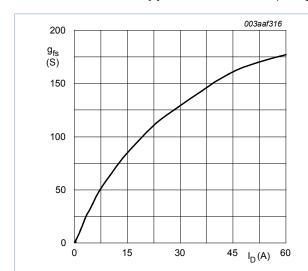


Fig. 6. Forward transconductance as a function of drain current; typical values

$$T_j = 25\,^{\circ}C; V_{DS} = 25V$$

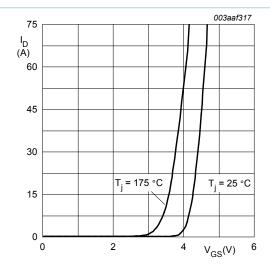


Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

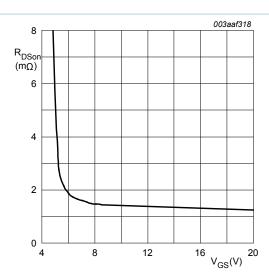
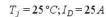


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values.



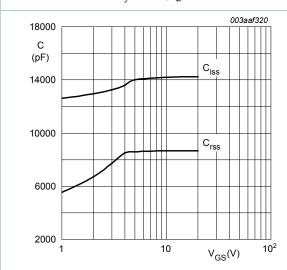


Fig. 10. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0V; f = 1MHz$$

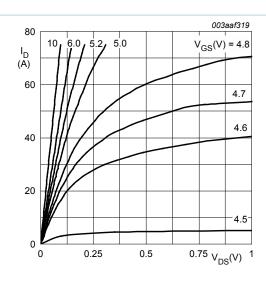


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25 \,^{\circ}C$$

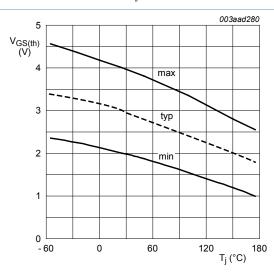


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

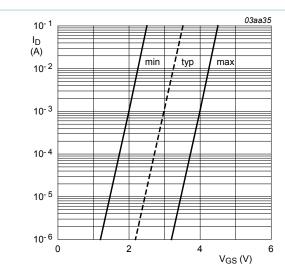


Fig. 12. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

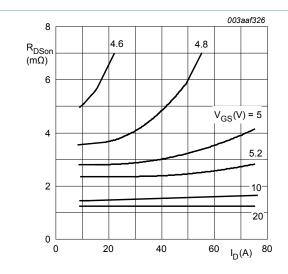


Fig. 14. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25$$
°C

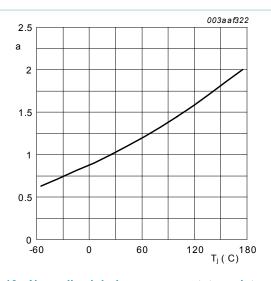


Fig. 13. Normalized drain-source on state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

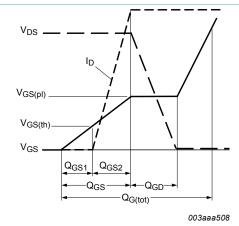


Fig. 15. Gate charge waveform definitions

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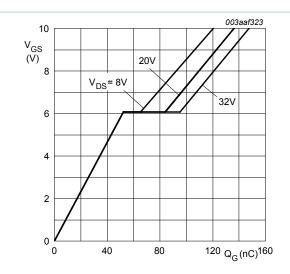


Fig. 16. Gate-source voltage as a function of gate charge; typical values

$$I_D = 75A$$

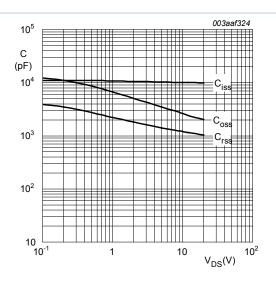


Fig. 17. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

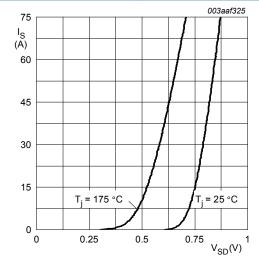
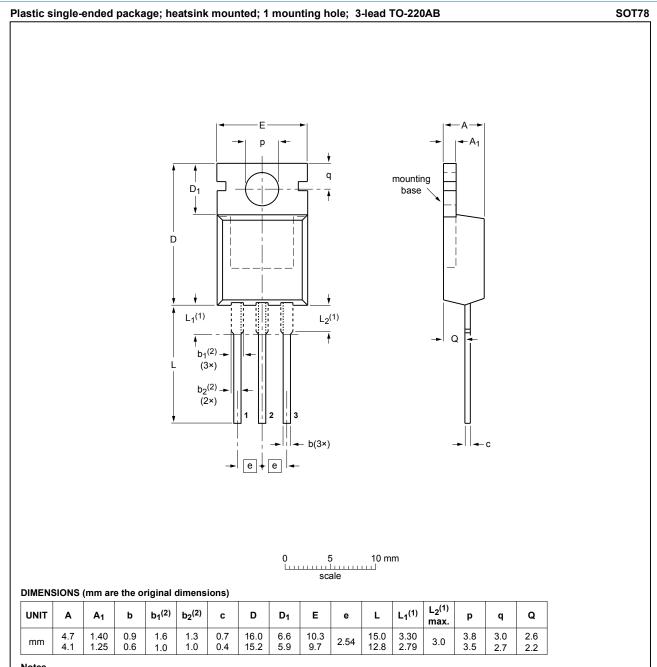


Fig. 18. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 V$$

11. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|---------|-----|-----------------|-------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | 1330E DATE |
| SOT78 | | 3-lead TO-220AB | SC-46 | | 08-04-23 08-06-13 |

Fig. 19. Package outline TO-220AB (SOT78)

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